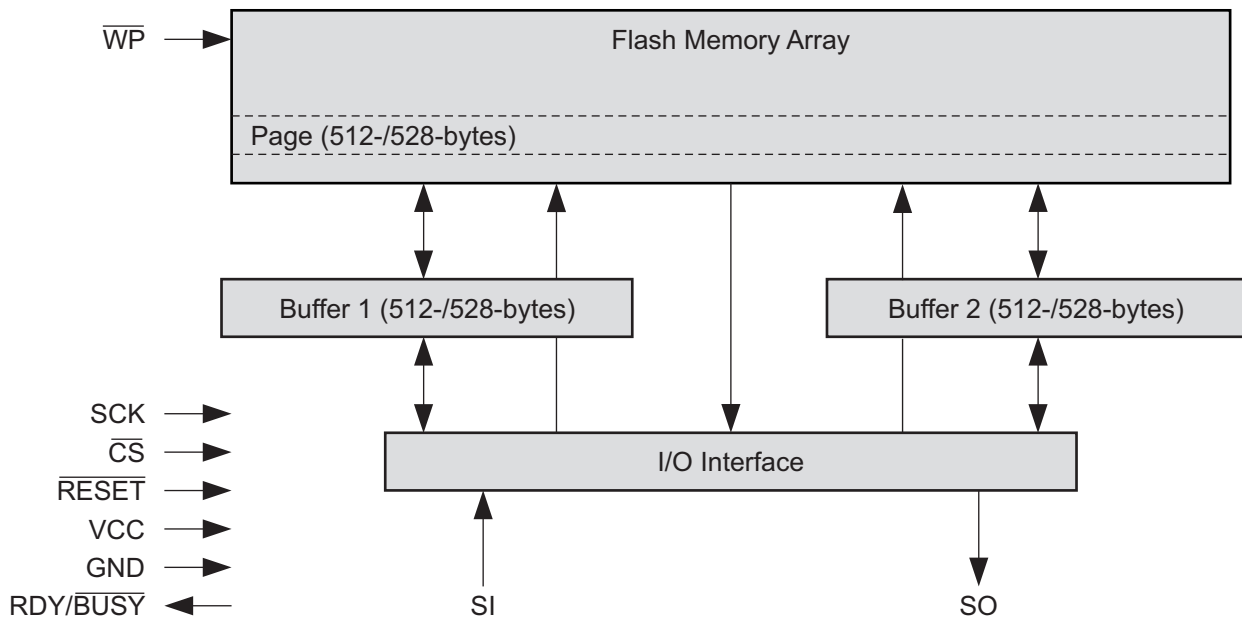


Figure 1-2. Block Diagram



2. Memory Array

To provide optimal flexibility, the AT45DB321D memory array is divided into three levels of granularity comprising sectors, blocks, and pages. The [“Memory Architecture Diagram”](#) illustrates the breakdown of each level, and details the number of pages per sector and block. All program operations to the DataFlash device occur on a page-by-page basis. The erase operations can be performed at the chip, sector, block, or page level.

Figure 2-1. Memory Architecture Diagram

